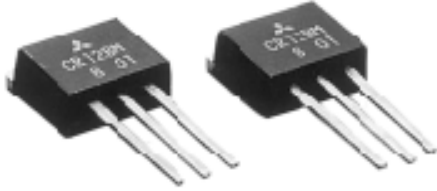


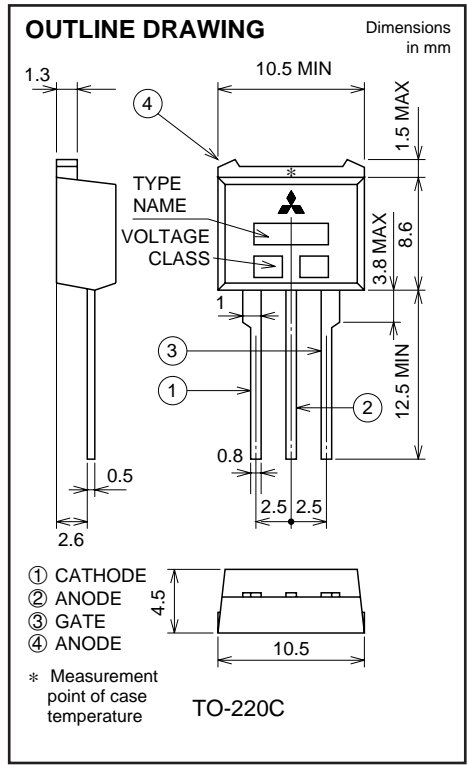
# CR12BM

MEDIUM POWER USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

**CR12BM**



- **IT (AV)** ..... **12A**
- **VDRM** ..... **400V/600V**
- **IGT** ..... **30mA**



## APPLICATION

Automatic strobe flasher

## MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
VRRM	Repetitive peak reverse voltage	400	600	V
VRSM	Non-repetitive peak reverse voltage	500	720	V
VR (DC)	DC reverse voltage	320	480	V
VDRM	Repetitive peak off-state voltage	400	600	V
VD (DC)	DC off-state voltage	320	480	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current		18.8	A
IT (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction, Tc=91°C	12.0	A
ITSM	Surge on-state current	60Hz sine half wave 1 full cycle, peak value, non-repetitive	360	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	544	A <sup>2</sup> s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VFGM	Peak gate forward voltage		6	V
VRGM	Peak gate reverse voltage		10	V
IFGM	Peak gate forward current		2	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	1.5	g

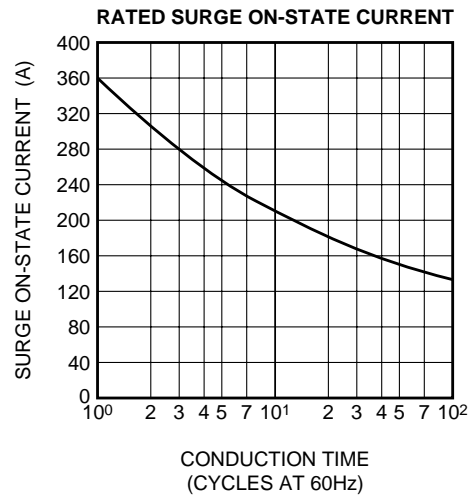
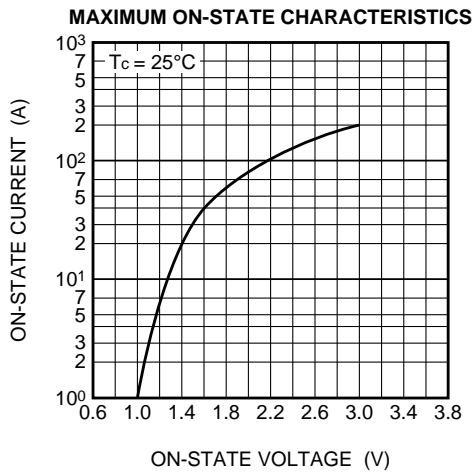
# CR12BM

MEDIUM POWER USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

## ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	$T_j=125^\circ\text{C}$ , $V_{\text{DRM}}$ applied	—	—	2.0	mA
IDRM	Repetitive peak off-state current	$T_j=125^\circ\text{C}$ , $V_{\text{DRM}}$ applied	—	—	2.0	mA
V <sub>TM</sub>	On-state voltage	$T_c=25^\circ\text{C}$ , $I_{\text{TM}}=40\text{A}$	—	—	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$T_j=25^\circ\text{C}$ , $V_D=6\text{V}$ , $I_T=1\text{A}$	—	—	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	$T_j=125^\circ\text{C}$ , $V_D=1/2V_{\text{DRM}}$	0.2	—	—	V
I <sub>GT</sub>	Gate trigger current	$T_j=25^\circ\text{C}$ , $V_D=6\text{V}$ , $I_T=1\text{A}$	—	—	30	mA
I <sub>H</sub>	Holding current	$T_j=25^\circ\text{C}$ , $V_D=12\text{V}$	—	15	—	mA
R <sub>th(j-c)</sub>	Thermal resistance	Junction to case	—	—	1.2	°C/W
R <sub>th(j-a)</sub>		Junction to ambient	—	—	70	

## PERFORMANCE CURVES

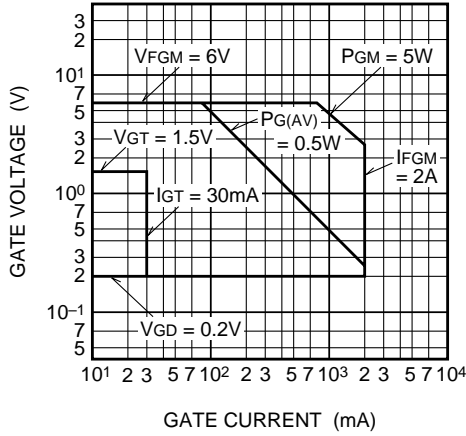


# CR12BM

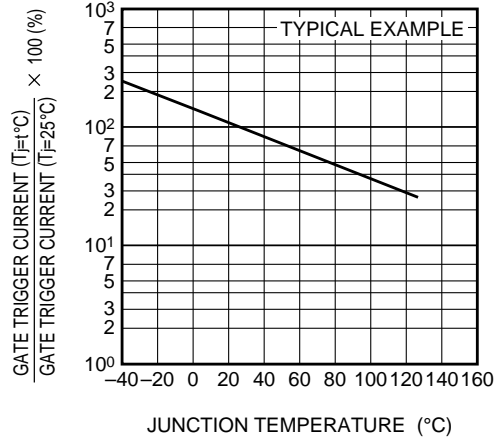
MEDIUM POWER USE

NON-INSULATED TYPE, GLASS PASSIVATION TYPE

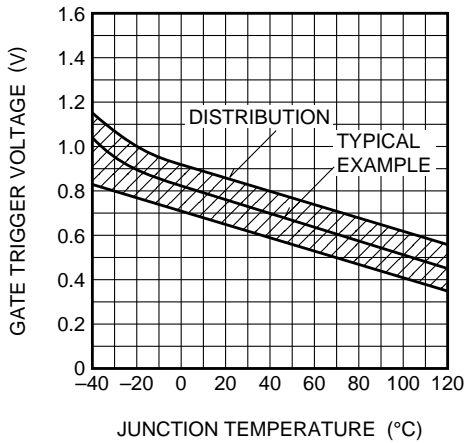
**GATE CHARACTERISTICS**



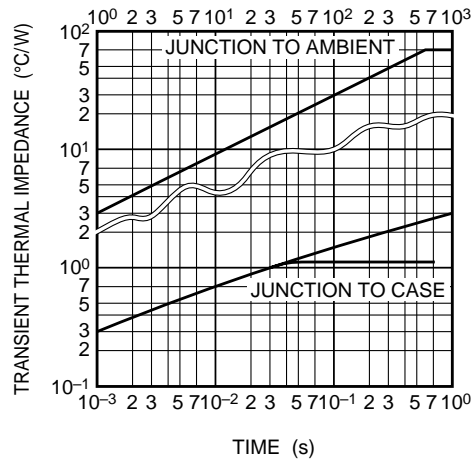
**GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE**



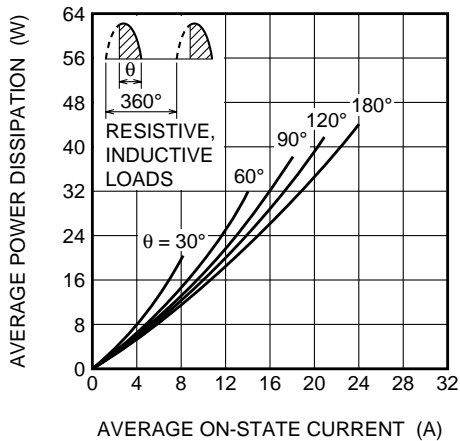
**GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE**



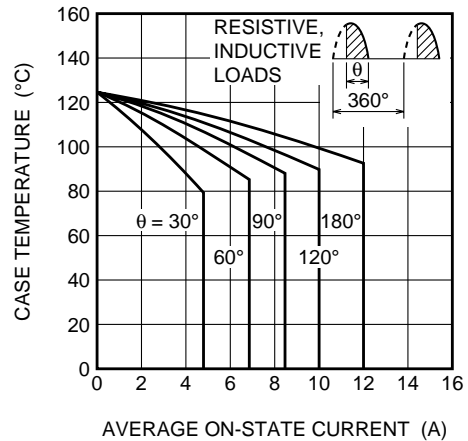
**MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS**



**MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE HALF WAVE)**



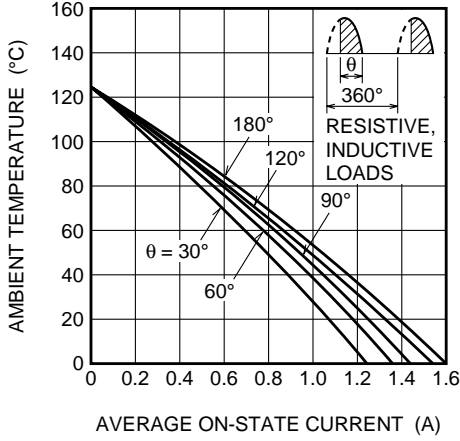
**ALLOWABLE CASE TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)**



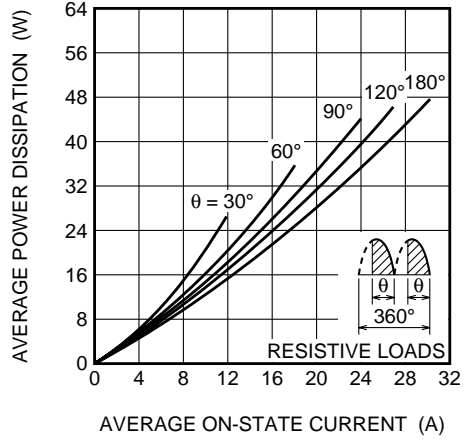
# CR12BM

MEDIUM POWER USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

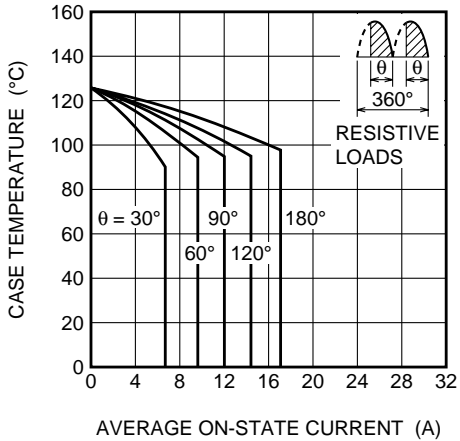
**ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE HALF WAVE)**



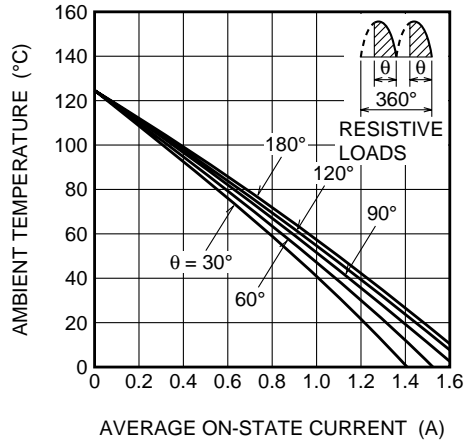
**MAXIMUM AVERAGE POWER DISSIPATION (SINGLE-PHASE FULL WAVE)**



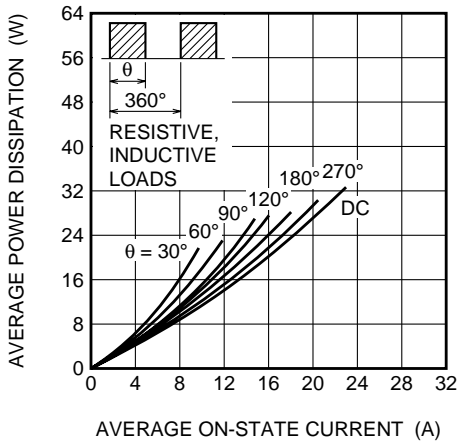
**ALLOWABLE CASE TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)**



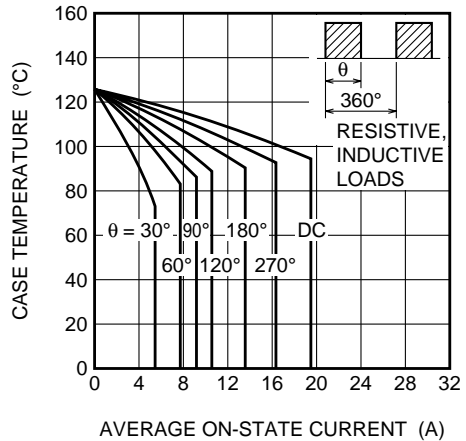
**ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (SINGLE-PHASE FULL WAVE)**



**MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)**



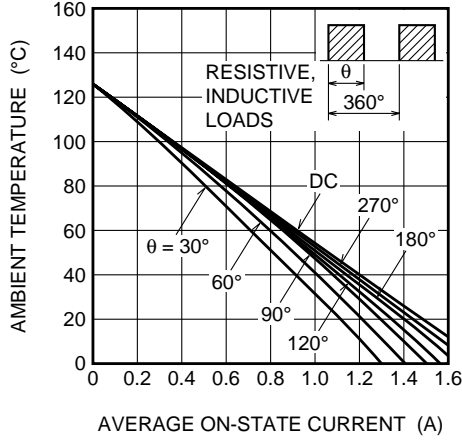
**ALLOWABLE CASE TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)**



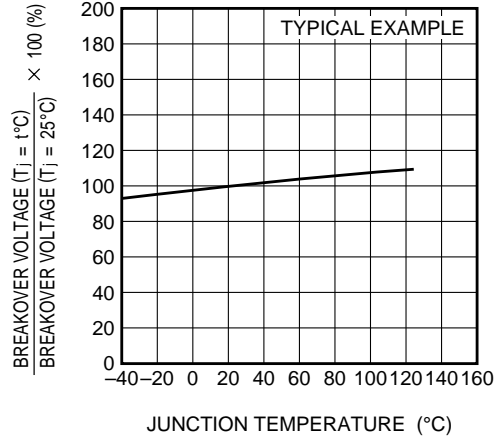
# CR12BM

MEDIUM POWER USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

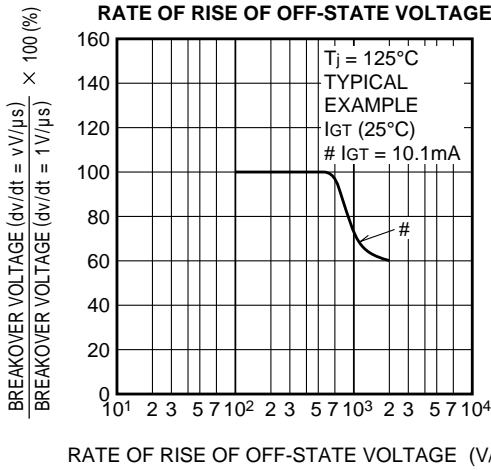
**ALLOWABLE AMBIENT TEMPERATURE VS. AVERAGE ON-STATE CURRENT (RECTANGULAR WAVE)**



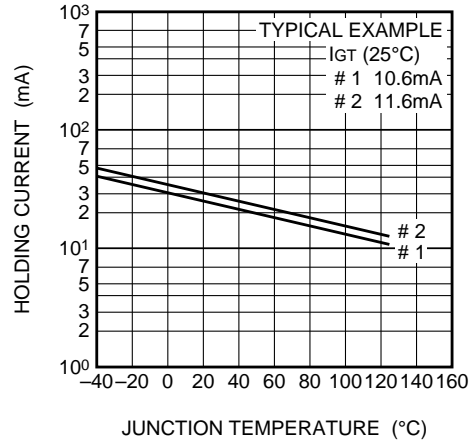
**BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE**



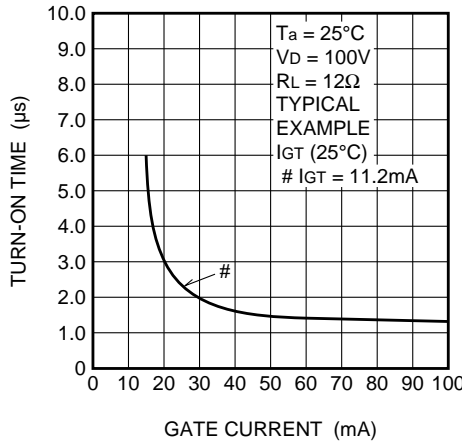
**BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE**



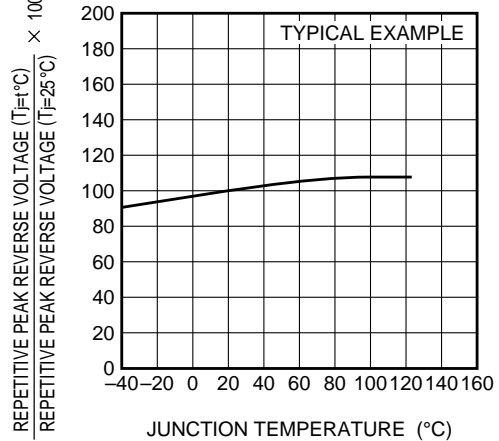
**HOLDING CURRENT VS. JUNCTION TEMPERATURE**



**TURN-ON TIME VS. GATE CURRENT**



**REPETITIVE PEAK REVERSE VOLTAGE VS. JUNCTION TEMPERATURE**



# CR12BM

MEDIUM POWER USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

